2SA608N TRANSISTOR (PNP)

TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- Large Current Capacity and Wide ASO.

APPLICATIONS

- Capable of Being Used in The Low Frequency to High Frequency Range.

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA608N	TO-92	Bulk	1000pcs/Bag
2SA608N-TA	TO-92	Tap	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-0.15	A
P_D	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

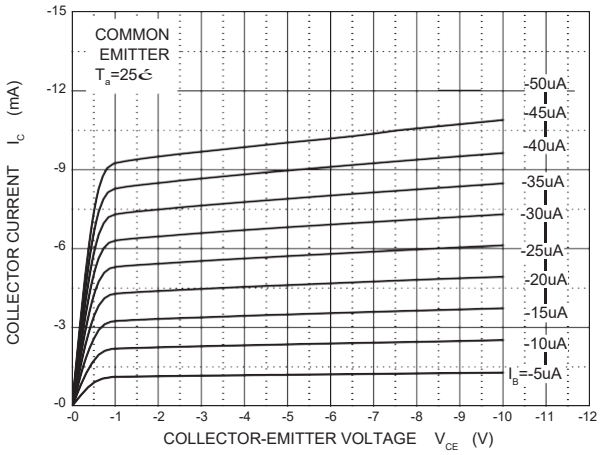
T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-0.01mA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-6V, I_C=-1mA	160		560	
	$h_{FE(2)}$	V_{CE}=-6V, I_C=-0.1mA	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.3	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C=-100mA,I_B=-10mA			-1	V
Collector output capacitance	C_{ob}	V_{CB}=-6V,I_C=0, f=1MHz		4.5		pF
Transition frequency	f_T	V_{CE}=-6V,I_C=-10mA		200		MHz

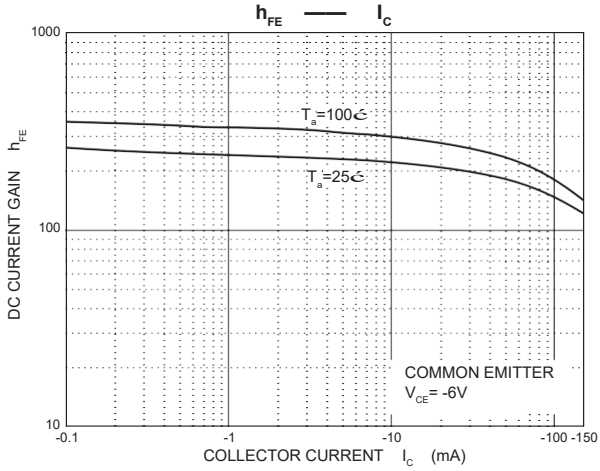
CLASSIFICATION OF $h_{FE(1)}$

RANK	F	G
RANGE	160-320	280-560

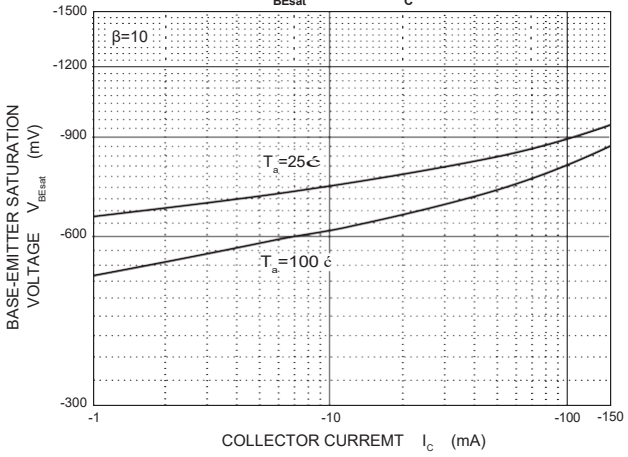
Static Characteristic



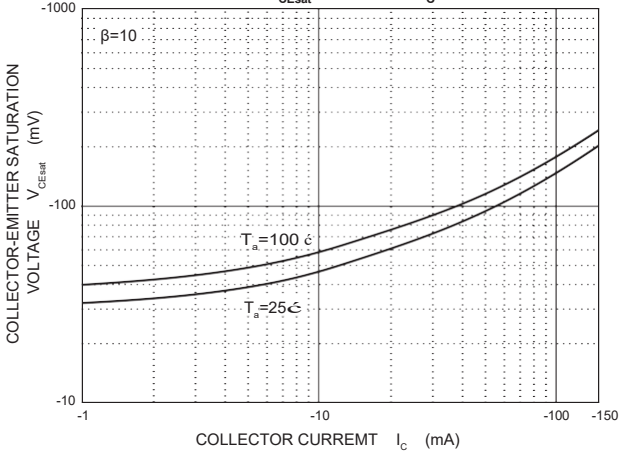
h_{FE} —— I_C



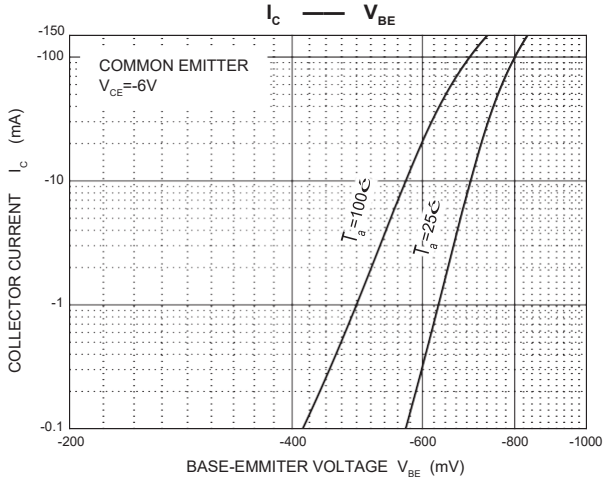
V_{BEsat} —— I_C



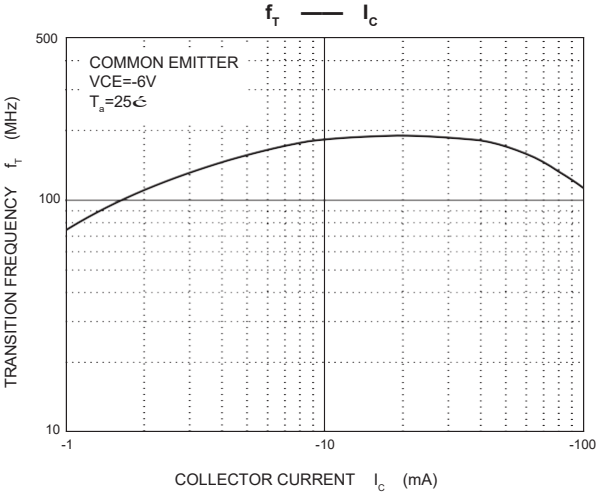
V_{CEsat} —— I_C



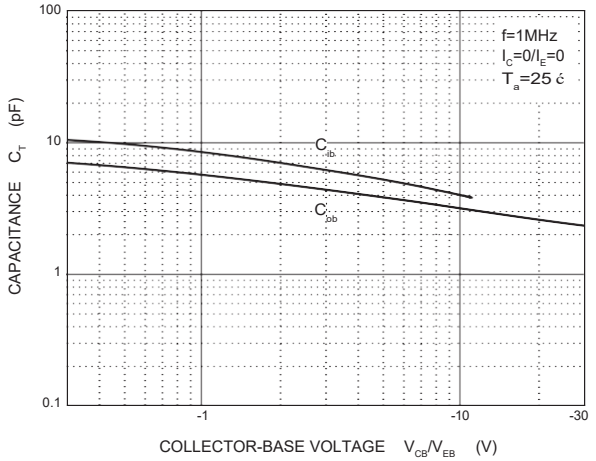
I_C —— V_{BE}



f_T —— I_C



C_{ob}/C_{ib} —— V_{CB}/V_{EB}



P_C —— T_a